

## **Amendments to the Claims**

This listing of claims will replace all prior versions, and listings, of claims in the application:

### **Listing of Claims**

1-16 (Canceled).

17. (Previously presented): A method of forming a tungsten silicide film, comprising:

disposing a substrate in a process chamber, the substrate having a film thereon comprising silicon;

subsequently opening a low stress valve having an outlet end connected to the process chamber, and an inlet end connected to a plurality of sources of gas via a gas inlet line, the sources of gas including a source of WF<sub>6</sub> gas and a source of an inert carrier gas;

controlling the flow of the WF<sub>6</sub> gas through the open low stress valve and into the process chamber using a mass flow controller disposed between the gas inlet line and the source of WF<sub>6</sub> gas;

subsequently closing the low stress valve to cut off the supplying of the WF<sub>6</sub> gas into the process chamber;

subsequently venting the gas inlet line to remove residual WF<sub>6</sub> gas therefrom;  
and

subsequently opening the low stress valve, and allowing the inert carrier gas to flow therethrough into the process chamber.